
2SK2796(L), 2SK2796(S)

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

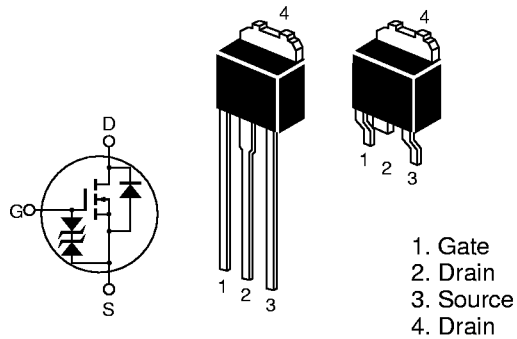
ADE-208-534C (Z)
4th. Edition
June 1, 1998

Features

- Low on-resistance
 $R_{DS(on)} = 0.12\Omega$ typ.
- 4V gate drive devices.
- High speed switching

Outline

DPAK | 1



2SK2796(L), 2SK2796(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current	I_D	5	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	20	A
Body-drain diode reverse drain current	I_{DR}	5	A
Avalanche current	I_{AP} ^{Note3}	5	A
Avalanche energy	E_{AR} ^{Note3}	2.14	mJ
Channel dissipation	P_{ch} ^{Note2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$
3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50\ \Omega$

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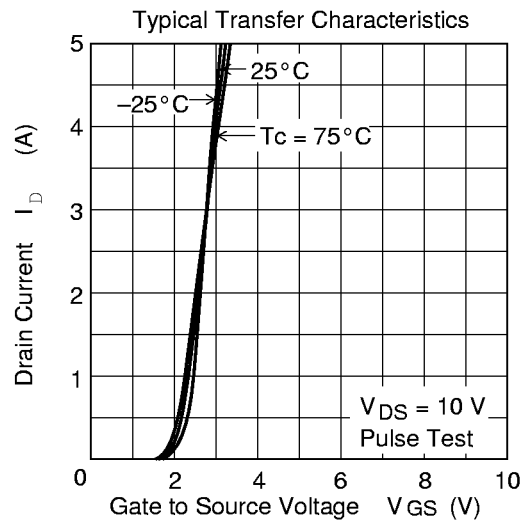
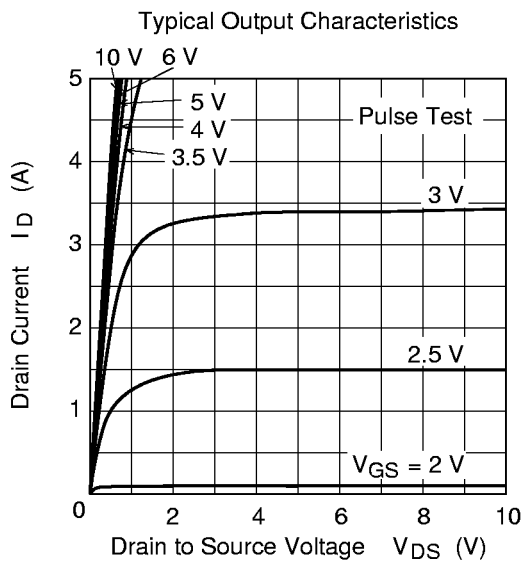
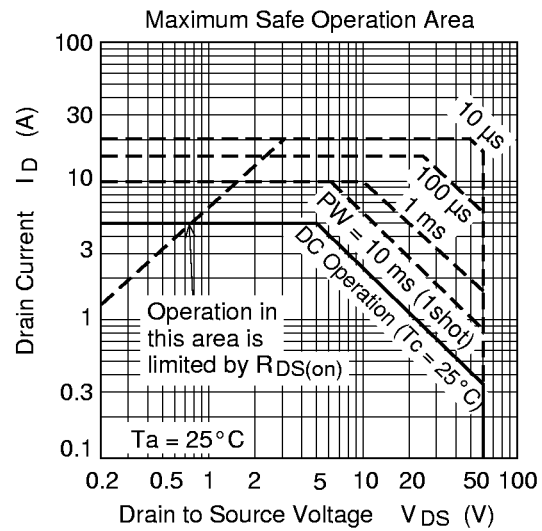
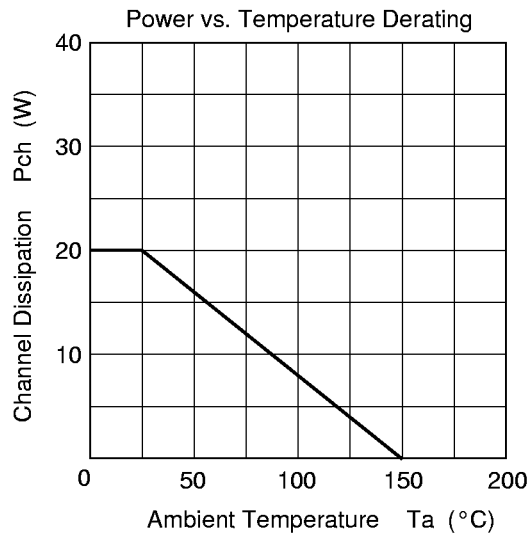
Electrical Characteristics (Ta = 25°C)

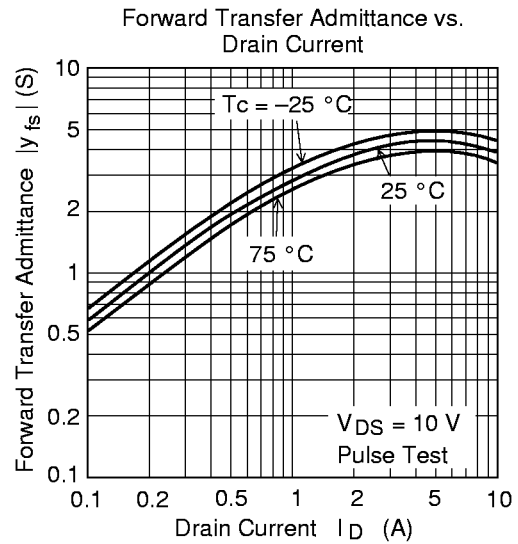
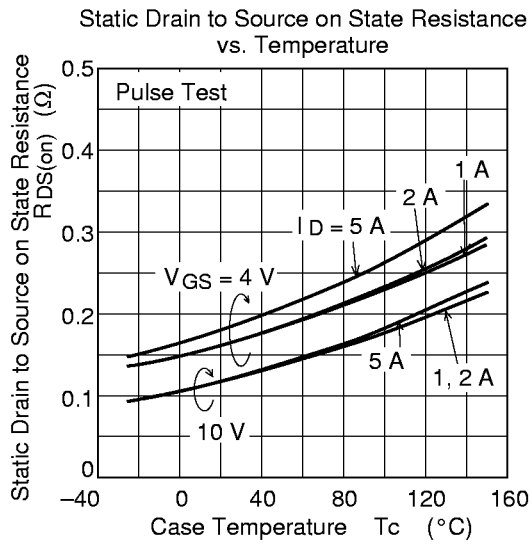
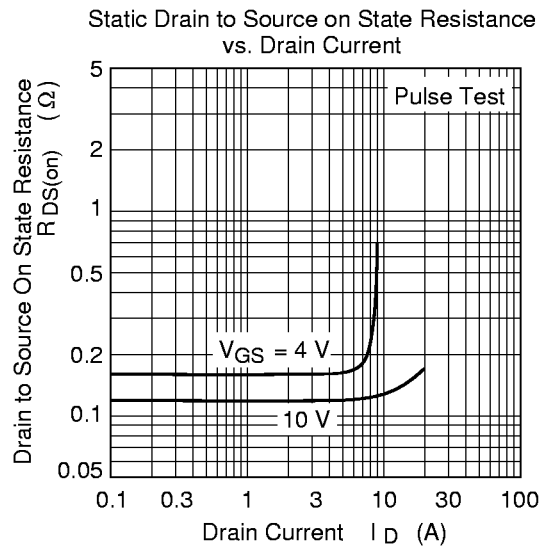
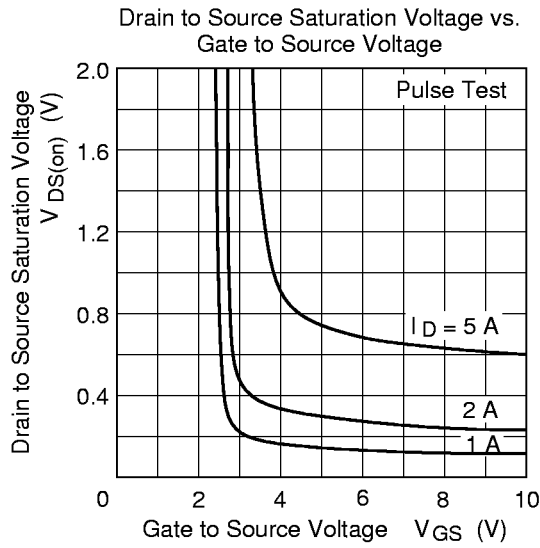
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10\text{mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\mu\text{A}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60\text{V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16\text{V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.16	Ω	$I_D = 3\text{A}$, $V_{GS} = 10\text{V}$ ^{Note4}
Static drain to source on state resistance	$R_{DS(on)}$	—	0.16	0.25	Ω	$I_D = 3\text{A}$, $V_{GS} = 4\text{V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	2.5	4.0	—	S	$I_D = 3\text{A}$, $V_{DS} = 10\text{V}$ ^{Note4}
Input capacitance	C_{iss}	—	180	—	pF	$V_{DS} = 10\text{V}$
Output capacitance	C_{oss}	—	90	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	30	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	9	—	ns	$V_{GS} = 10\text{V}$, $I_D = 3\text{A}$
Rise time	t_r	—	25	—	ns	$R_L = 10\Omega$
Turn-off delay time	$t_{d(off)}$	—	35	—	ns	
Fall time	t_f	—	55	—	ns	
Body-drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 5\text{A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	40	—	ns	$I_F = 5\text{A}$, $V_{GS} = 0$ $diF/dt = 50\text{A}/\mu\text{s}$

Note: 4. Pulse test

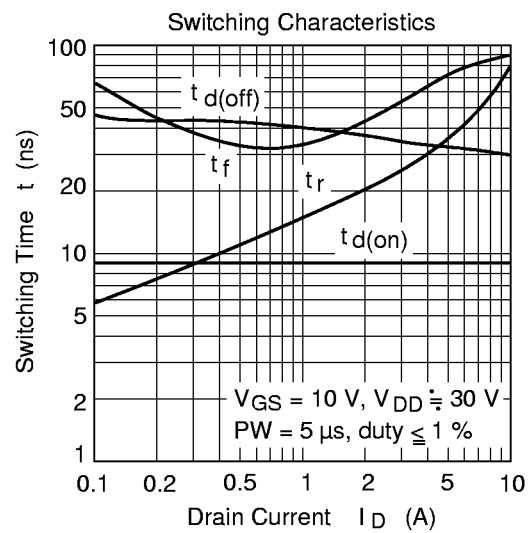
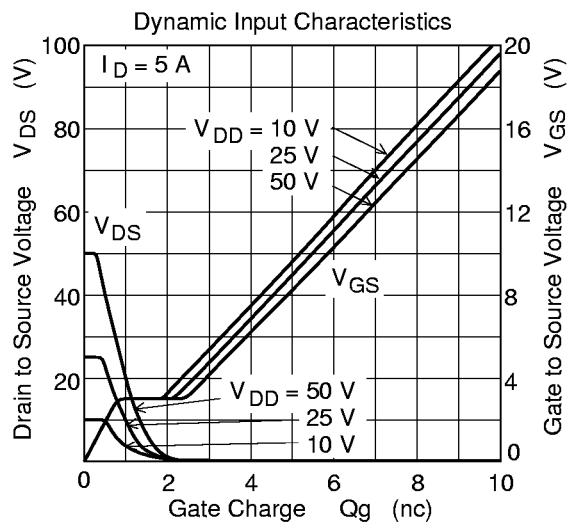
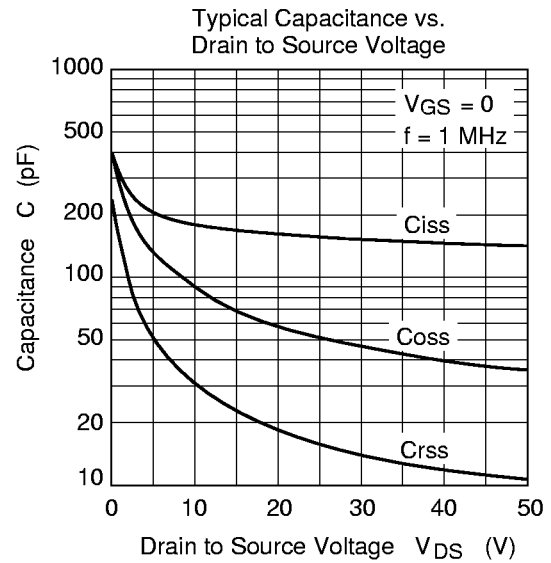
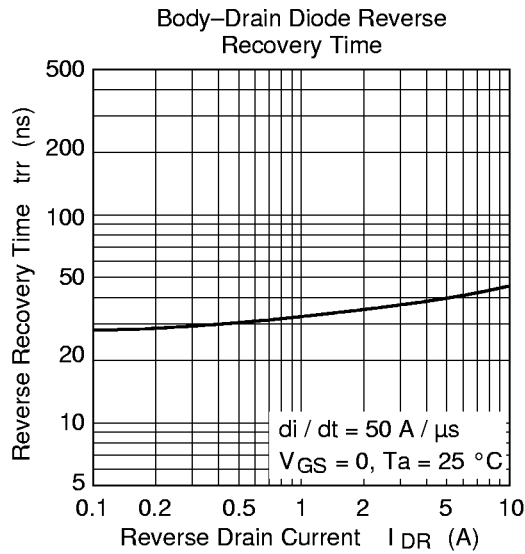
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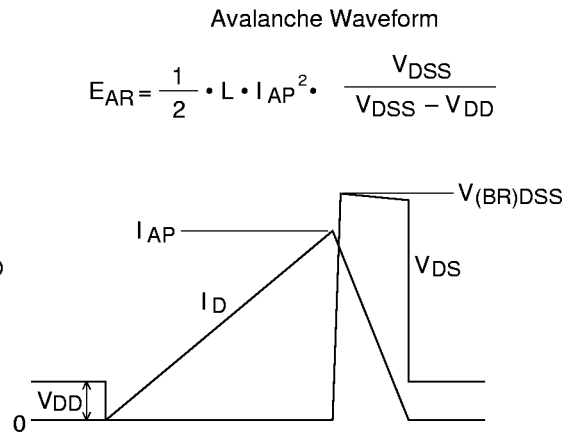
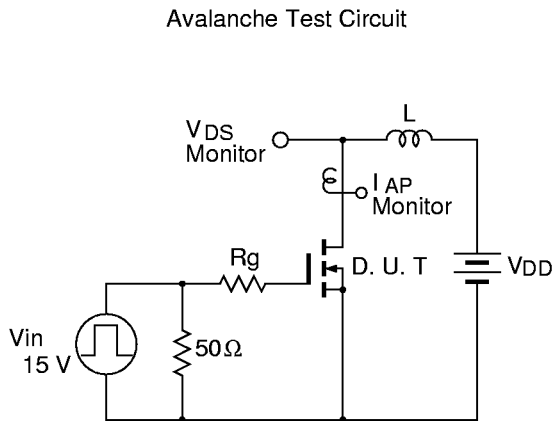
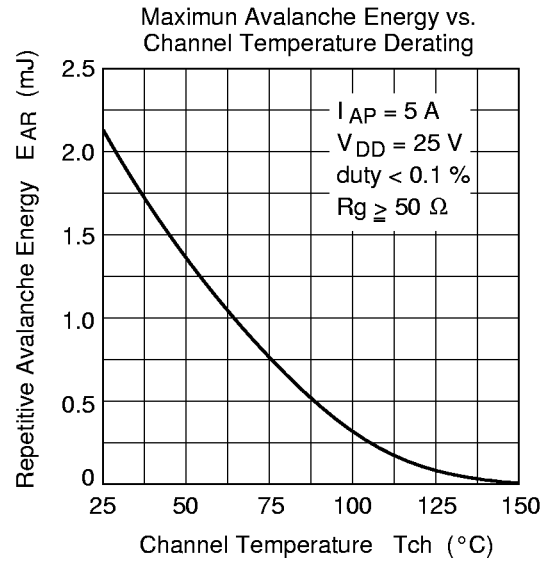
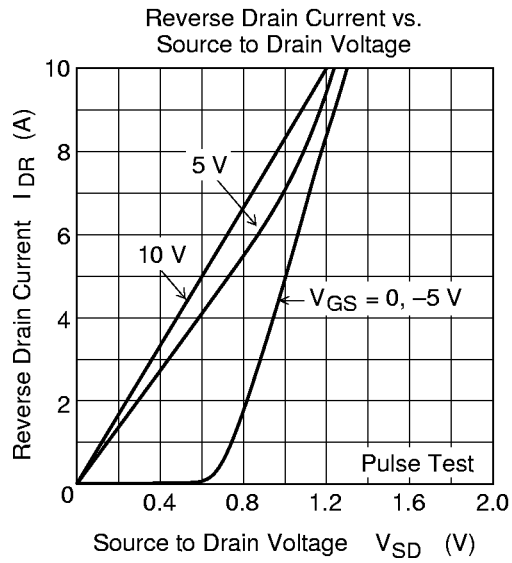
Main Characteristics



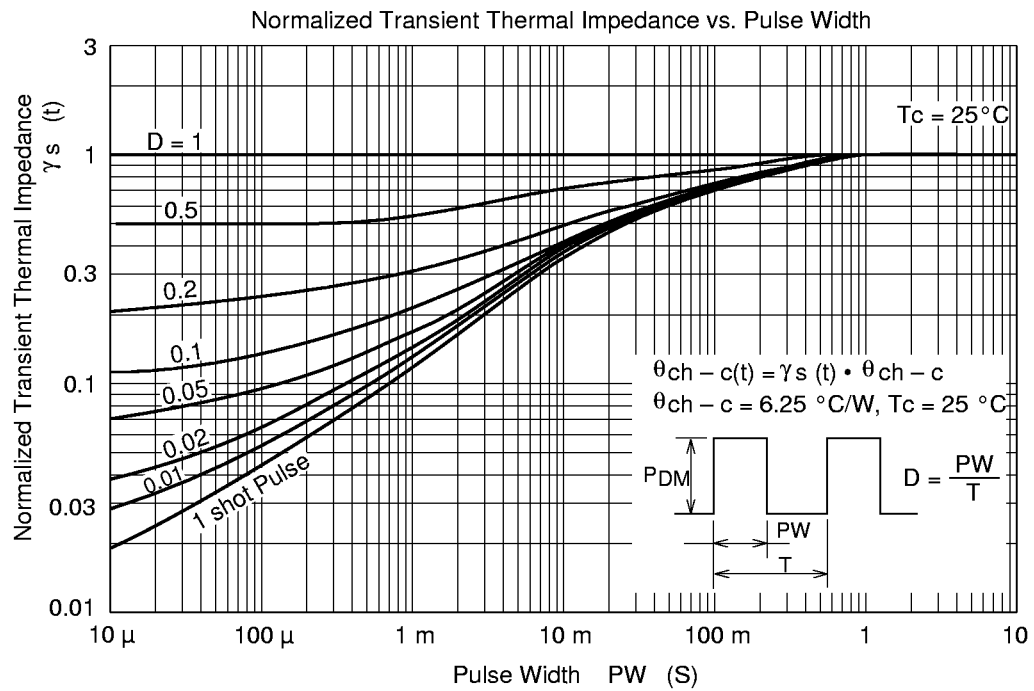


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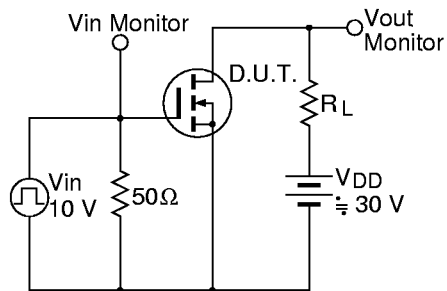




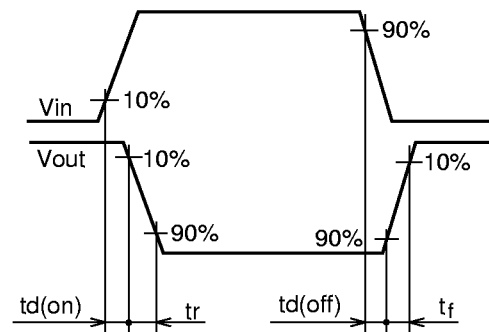
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Switching Time Test Circuit

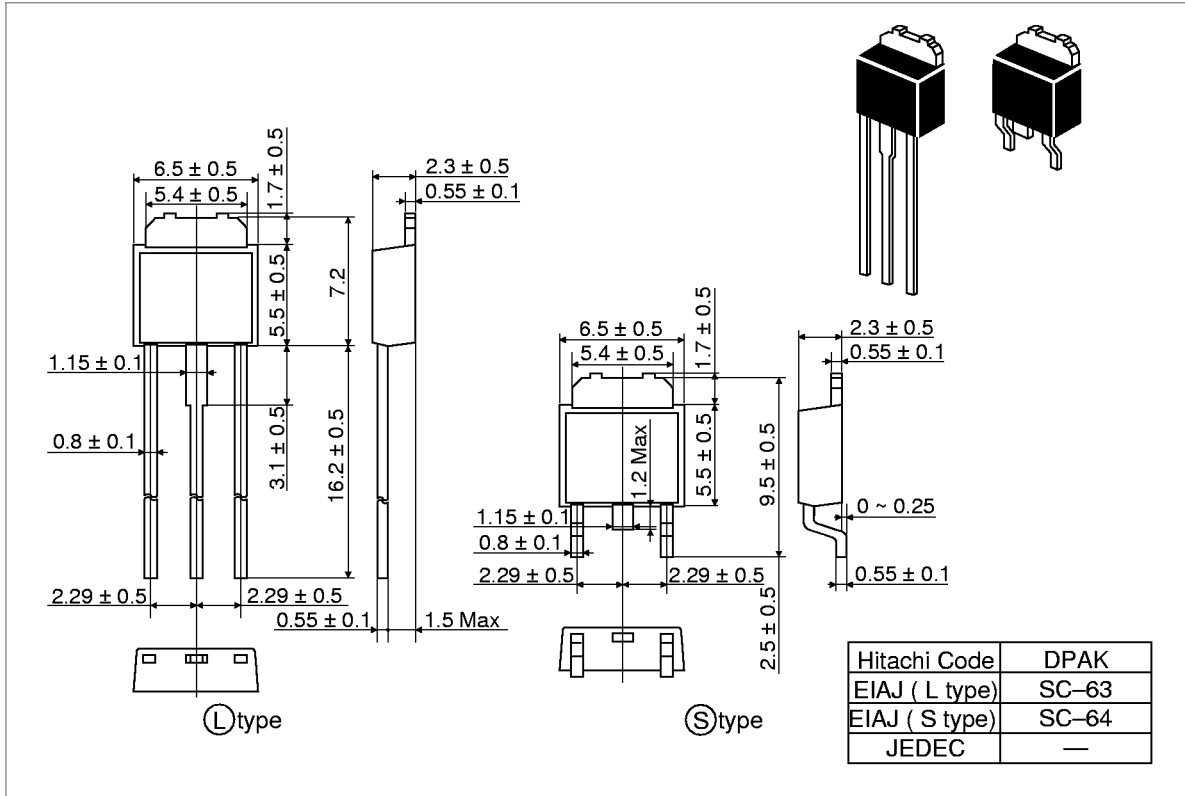


Waveform



2SK2796(L), 2SK2796(S)

Package Dimensions (Unit: mm)



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Cautions

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